

New Jersey Semi-Conductor Products, Inc.

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Silicon NPN Power Transistor**2SC4533****DESCRIPTION**

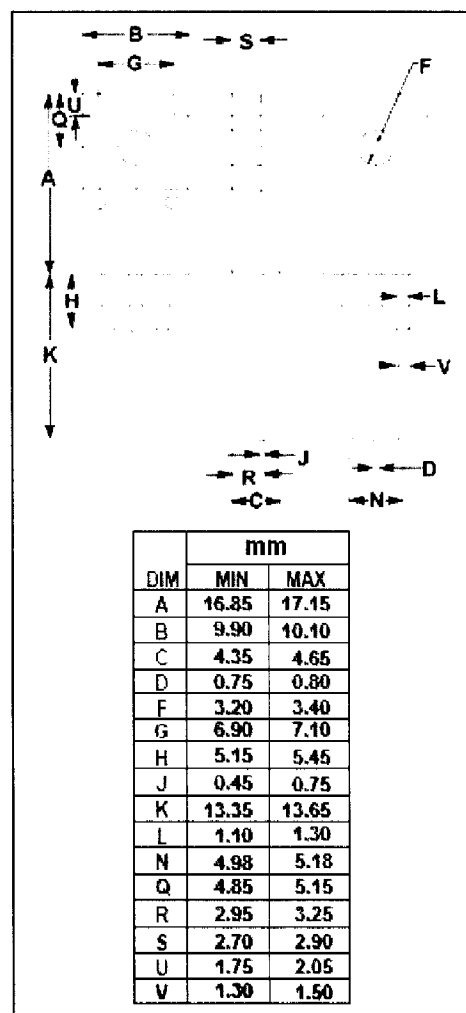
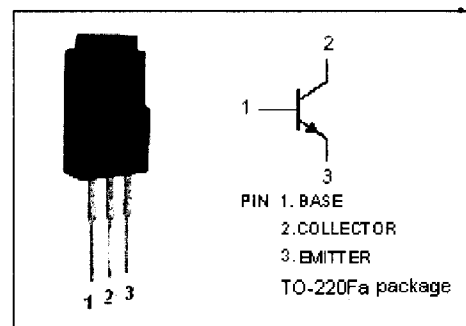
- Collector-Base Breakdown Voltage-
 : $V_{(BR)CBO} = 500V(\text{Min.})$
- Wide Area of Safe Operation
- High Speed Switching

APPLICATIONS

- Designed for high speed switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CES}	Collector-Emitter Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	6	A
I_B	Base Current-Continuous	1.2	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	30	
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



Quality Semi-Conductors

Silicon NPN Power Transistor

2SC4533

ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	400			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1.5\text{A}; I_B=0.3\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1.5\text{A}; I_B=0.3\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			100	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			100	μA
h_{FE-1}	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=5\text{V}$	10			
h_{FE-2}	DC Current Gain	$I_C=1.5\text{A}; V_{CE}=5\text{V}$	8		40	
f_T	Current-Gain—Bandwidth Product	$I_C=0.2\text{A}; V_{CE}=10\text{V}; f=1\text{MHz}$		10		MHz

Switching Times

t_{on}	Turn-on Time	$I_C=1.5\text{A}; I_{B1}=0.15\text{A}; I_{B2}=-0.3\text{A}; V_{CC}=200\text{V}$			1.0	μs
t_s	Storage Time				3.0	μs
t_f	Fall Time				0.3	μs